

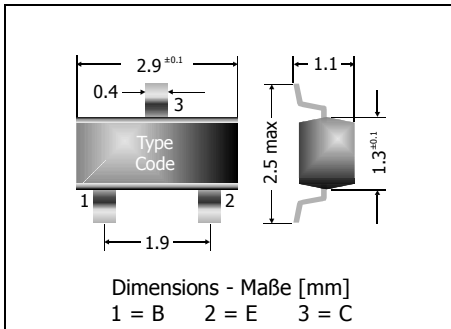
## BCV26

PNP

**Surface Mount Darlington Si-Epi-Planar Transistors**  
**Si-Epi-Planar Darlington-Transistoren für die Oberflächenmontage**

PNP

Version 2010-07-14



Power dissipation – Verlustleistung

200 mW

Plastic case  
KunststoffgehäuseSOT-23  
(TO-236)

Weight approx. – Gewicht ca.

0.01 g

Plastic material has UL classification 94V-0  
Gehäusematerial UL94V-0 klassifiziertStandard packaging taped and reeled  
Standard Lieferform getupet auf Rolle

### Maximum ratings (T<sub>A</sub> = 25°C)

### Grenzwerte (T<sub>A</sub> = 25°C)

			BCV26
Collector-Emitter-volt. – Kollektor-Emitter-Spannung	B open	- V <sub>CEO</sub>	30 V
Collector-Base-voltage – Kollektor-Basis-Spannung	E open	- V <sub>CBO</sub>	40 V
Emitter-Base-voltage – Emitter-Basis-Spannung	C open	- V <sub>EBO</sub>	10 V
Power dissipation – Verlustleistung		P <sub>tot</sub>	200 mW <sup>1)</sup>
Collector current – Kollektorstrom (dc)		- I <sub>C</sub>	500 mA
Junction temperature – Sperrschichttemperatur		T <sub>j</sub>	-55...+150°C
Storage temperature – Lagerungstemperatur		T <sub>s</sub>	-55...+150°C

### Characteristics (T<sub>j</sub> = 25°C)

### Kennwerte (T<sub>j</sub> = 25°C)

		Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis <sup>2)</sup>				
- V <sub>CE</sub> = 5 V, - I <sub>C</sub> = 1 mA	h <sub>FE</sub>	4000	–	–
- V <sub>CE</sub> = 5 V, - I <sub>C</sub> = 10 mA	h <sub>FE</sub>	10000	–	–
- V <sub>CE</sub> = 5 V, - I <sub>C</sub> = 100 mA	h <sub>FE</sub>	20000	–	–
Collector-Emitter saturation voltage – Kollektor-Emitter-Sättigungsspg. <sup>2)</sup>				
- I <sub>C</sub> = 100 mA, - I <sub>B</sub> = 0.1 mA	- V <sub>CEsat</sub>	–	–	1.0 V
Base-Emitter saturation voltage – Basis-Emitter-Sättigungsspannung <sup>2)</sup>				
- I <sub>C</sub> = 100 mA, - I <sub>B</sub> = 0.1 mA	- V <sub>BEsat</sub>	–	–	1.5 V

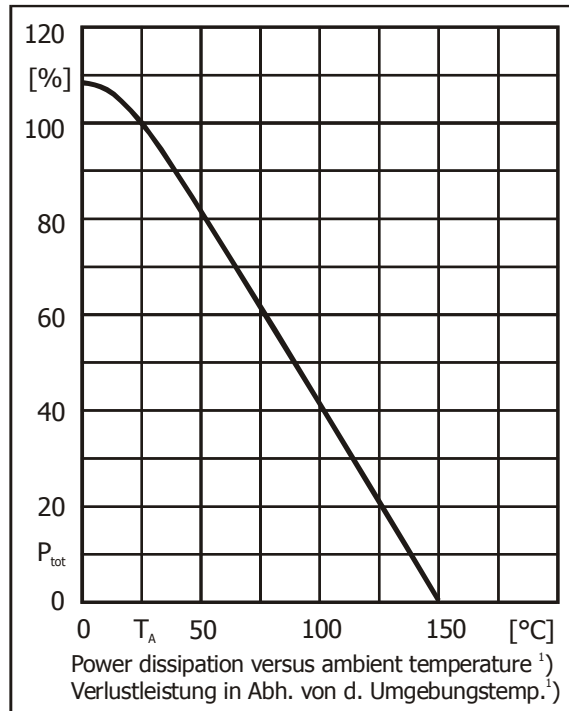
1 Mounted on P.C. board with 3 mm<sup>2</sup> copper pad at each terminal  
 Montage auf Leiterplatte mit 3 mm<sup>2</sup> Kupferbelag (Löt-pad) an jedem Anschluss

2 Tested with pulses t<sub>p</sub> = 300 μs, duty cycle ≤ 2% – Gemessen mit Impulsen t<sub>p</sub> = 300 μs, Schaltverhältnis ≤ 2%

**Characteristics (T<sub>j</sub> = 25°C)**

**Kennwerte (T<sub>j</sub> = 25°C)**

Collector-Base cutoff current – Kollektor-Basis-Reststrom - V <sub>CB</sub> = 30 V, (E open)	- I <sub>CBO</sub>	-	-	100 nA
Emitter-Base-cutoff current – Emitter-Basis-Reststrom - V <sub>EB</sub> = 10 V, (C open)	- I <sub>EBO</sub>	-	--	100 nA
Gain-Bandwidth Product – Transitfrequenz - I <sub>C</sub> = 5 mA, - V <sub>CE</sub> = 30 V, f = 100 MHz	f <sub>T</sub>	-	220 MHz	-
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R <sub>thA</sub>	< 420 K/W <sup>1)</sup>		



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